



N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.0095 at $V_{GS} = 10$ V	13
	0.0105 at $V_{GS} = 4.5$ V	12

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.53 V at 3.0 A	3.0

FEATURES

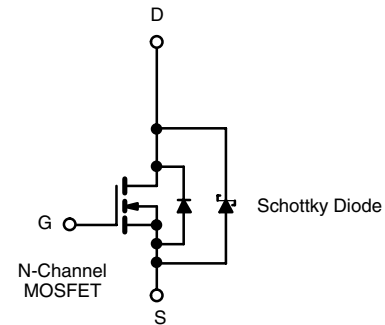
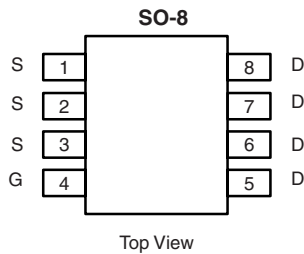
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- LITTLE FOOT[®] Plus Schottky
- Shoot-Thru-Free
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- DC/DC Converters Optimized for "Low-Side" Synchronous Rectifier Operation



Ordering Information: Si4736DY-T1-E3 (Lead (Pb)-free)
Si4736DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	30		V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	13	9	A
		$T_A = 70$ °C	10	7	
Pulsed Drain Current	I_{DM}	50			
Continuous Source Current (Diode Conduction) ^a	I_S	5	3.0		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.1	1.40	W
		$T_A = 70$ °C	2.0	0.90	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	33	40	°C/W
		Steady State	70	85	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

This data sheet contains preliminary specifications that are subject to change.

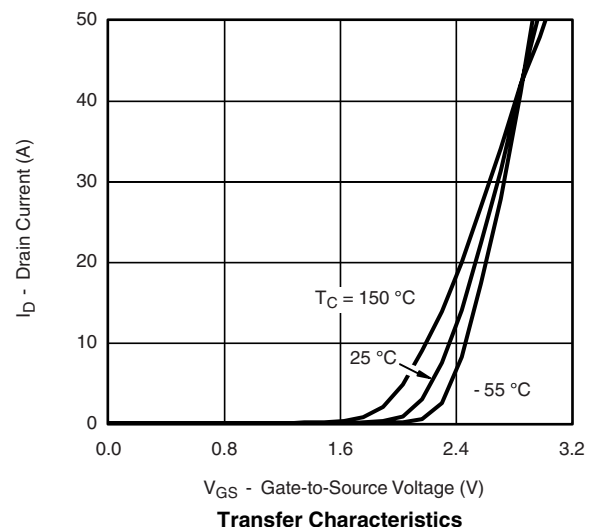
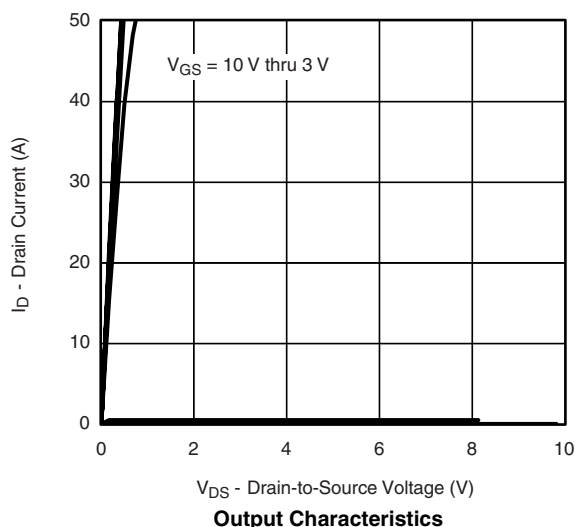
MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.8	1.35	1.9	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}$		0.007	0.100	mA
		$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 100\text{ }^\circ\text{C}$		1.5	10	
		$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 125\text{ }^\circ\text{C}$		6.5	20	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	20			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 13\ \text{A}$		0.0070	0.0095	Ω
		$V_{GS} = 4.5\ \text{V}, I_D = 12\ \text{A}$		0.0083	0.0105	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\ \text{V}, I_D = 13\ \text{A}$		56		S
Diode Forward Voltage ^b	V_{SD}	$I_S = 3.0\ \text{A}, V_{GS} = 0\ \text{V}$		0.495	0.53	V
		$I_S = 3.0\ \text{A}, V_{GS} = 0\ \text{V}, T_J = 125\text{ }^\circ\text{C}$		0.430	0.47	
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 13\ \text{A}$		37	55	nC
Gate-Source Charge	Q_{gs}		10			
Gate-Drain Charge	Q_{gd}		8.8			
Gate Resistance	R_g			0.8		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_g = 6\ \Omega$		17	26	ns
Rise Time	t_r		14	21		
Turn-Off Delay Time	$t_{d(off)}$		102	155		
Fall Time	t_f		26	40		
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = 3.0\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		42	

Notes:

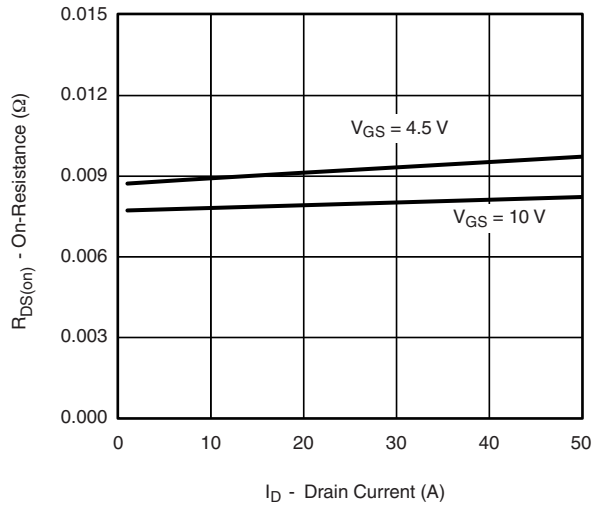
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

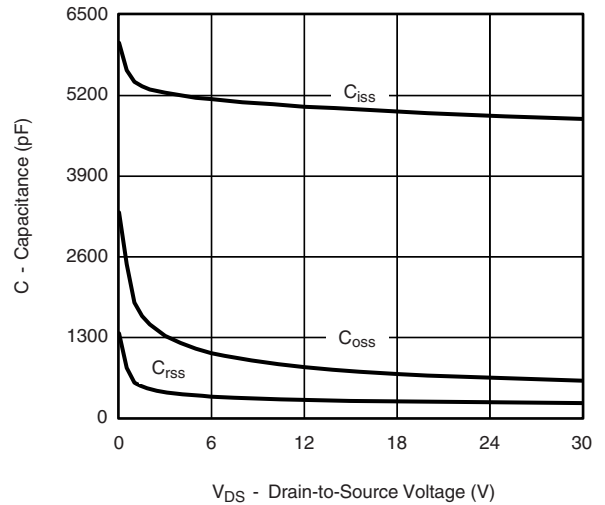
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$ unless otherwise noted



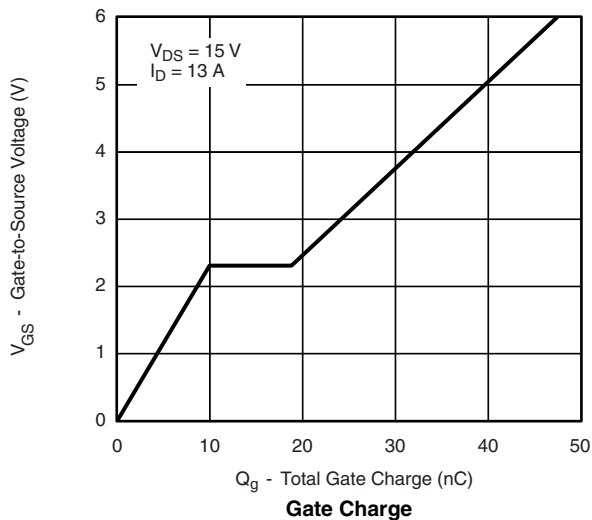
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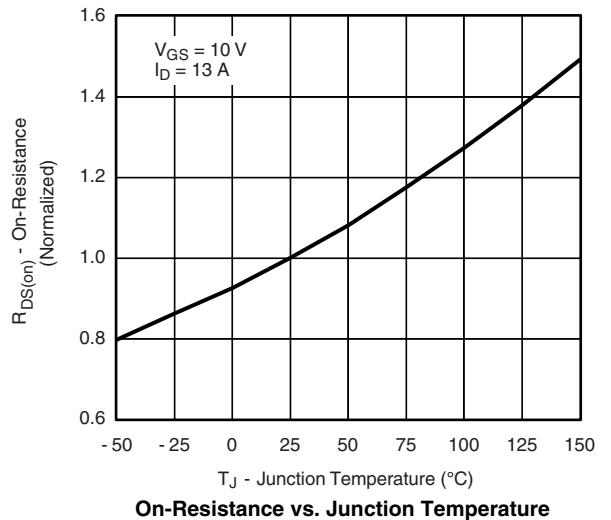
On-Resistance vs. Drain Current



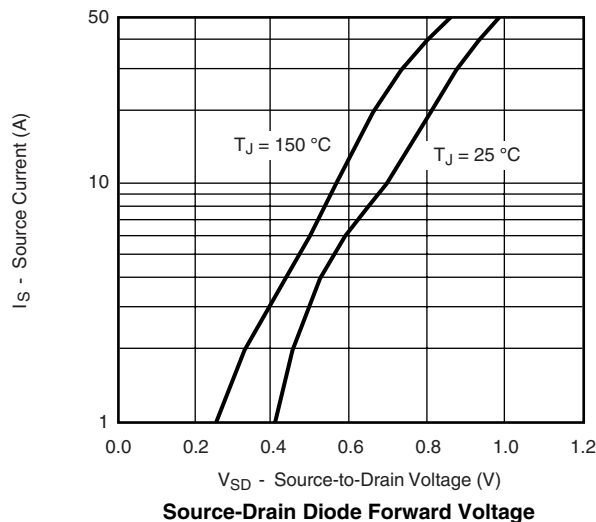
Capacitance



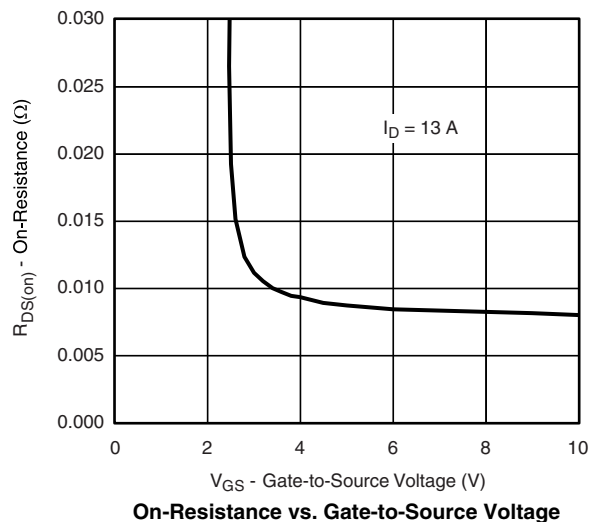
Gate Charge



On-Resistance vs. Junction Temperature

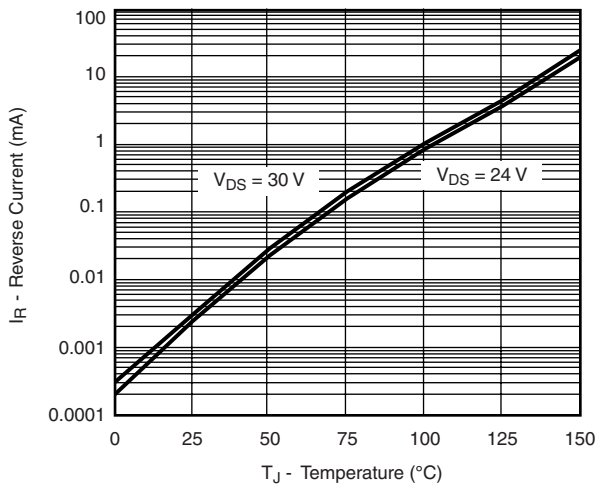


Source-Drain Diode Forward Voltage

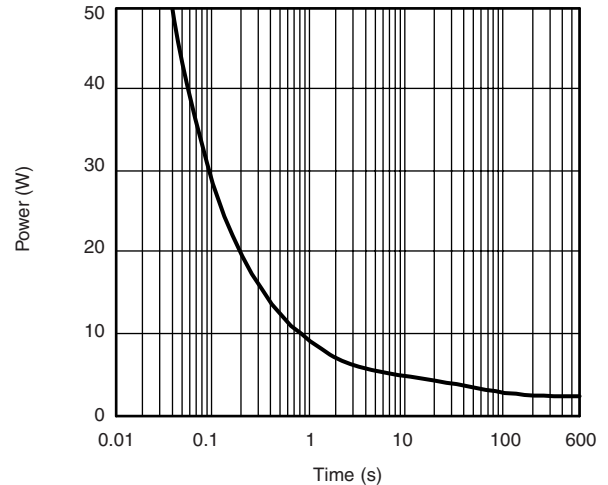


On-Resistance vs. Gate-to-Source Voltage

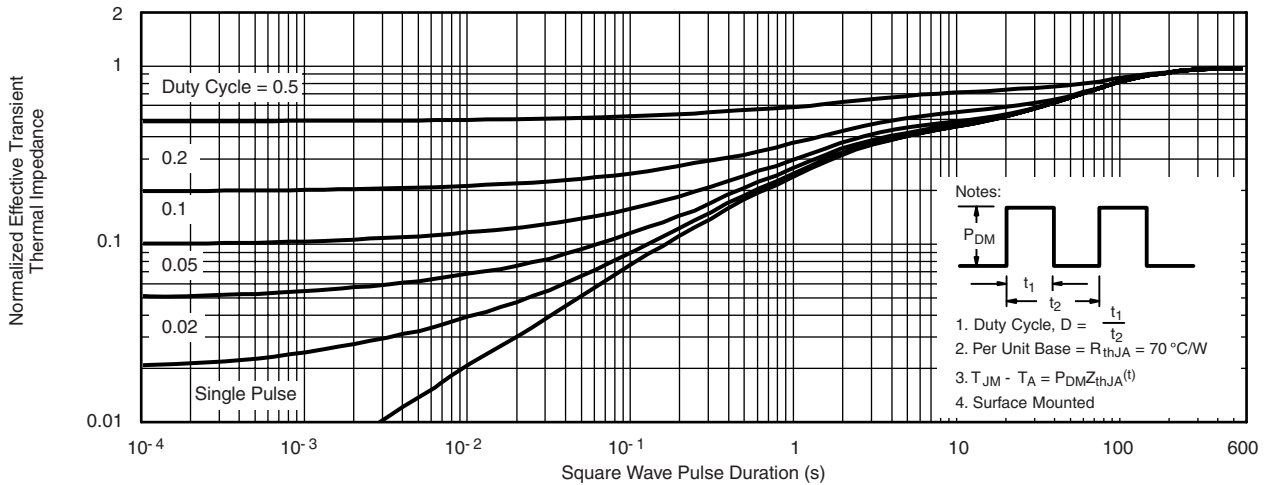
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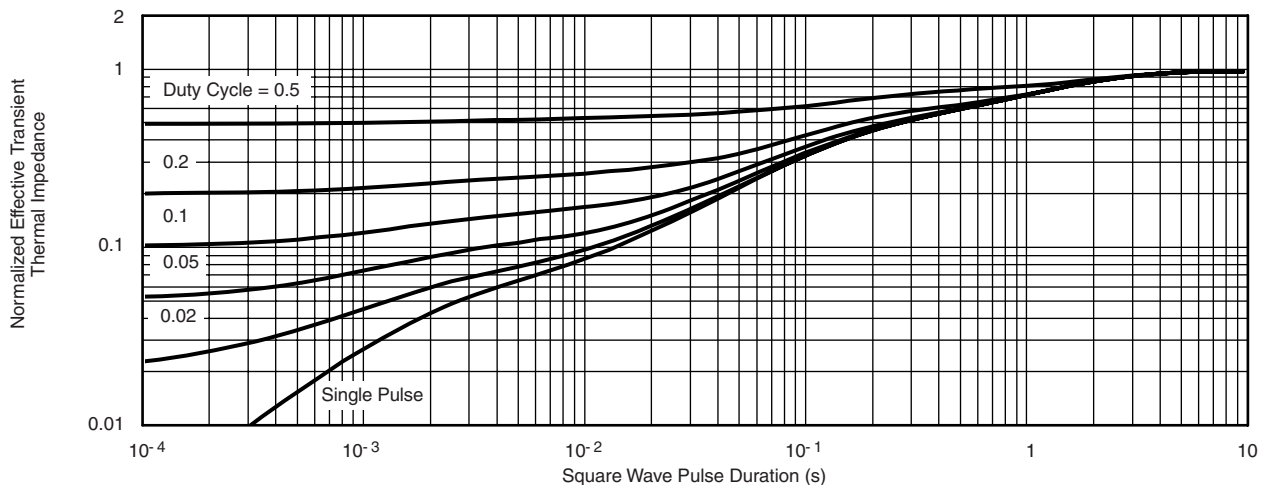
Reverse Current vs. Junction Temperature



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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